

Form (Rev. 2/01)

UNITED STATES

Docket No.: 1514.1033

COMBINED DECLARATION/POWER OF ATTORNEY FOR UTILITY/DESIGN PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

POLYCRYSTALLINE SILICON THIN FILM FABRICATION METHOD THEREOF, AND THIN FILM TRANSISTOR WITHOUT DIRECTIONAL DEPENDENCY ON ACTIVE CHANNELS FABRICATED USING THE SAME

the specification of which is attached hereto, unless the following box is checked:

☐ was filed on as United States Application Number (i) PCT International Application Number TO BE ASSIGNED and was amended on (if applicable).

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 C.F.R. § 1.56.

I hereby claim foreign priority benefit(s) under 35 U.S.C. § 119(a)-(d) or § 365(a)-(c) of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application(s) for patent or inventor's certificate having a filing date before that of the application on which priority is claimed.

Prior Foreign Application(s)Priority NOT
Claimed

<u>2003-13829</u>	<u>Republic of Korea</u>	<u>5/March/2003</u>	<input type="checkbox"/>
(Number)	(Country)	Day/Month/Year Filed	
<u> </u>	<u> </u>	<u> </u>	<input type="checkbox"/>
(Number)	(Country)	Day/Month/Year Filed	

I hereby claim the benefit under 35 U.S.C. § 120 or § 119(c) of any United States application(s), or § 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application(s) in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 C.F.R. § 1.56 which became available between the filing date of the prior application and the national or PCT International filing date of this application.

(Application Serial No.)

(Filing Date)

(Status — patented, pending, abandoned)

(Application Serial No.)

(Filing Date)

(Status — patented, pending, abandoned)

I hereby appoint the attorneys and agents of Staats & Halsey LLP under USPTO Customer No. 21,171 to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

21171
PATENT TRADEMARK OFFICE

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Full name of sole or first inventor PARK, Ji YoungInventor's Signature Ji-Young ParkDate October 28, 2003Residence Siwon-city, KoreaCitizenship Republic of KoreaMailing Address 993-5, Youngtong-dong, Paldal-gu, Siwon-city, Gyeonggi-do, KoreaFull name of second inventor PARK, Hye HwangInventor's Signature Hye Hwang ParkDate October 28, 2003Residence Siwon-city, KoreaCitizenship Republic of KoreaMailing Address 1285-7, Gwonseon-dong, Gwonseon-gu, Siwon-city, Gyeonggi-do, Korea☐ Additional inventors are being named on separately numbered sheets attached hereto.